# Laboratoire Plasma et Conversion d'Energie



# Effect of the operating parameters on aerosol-assisted atmospheric pressure plasma thin film deposition

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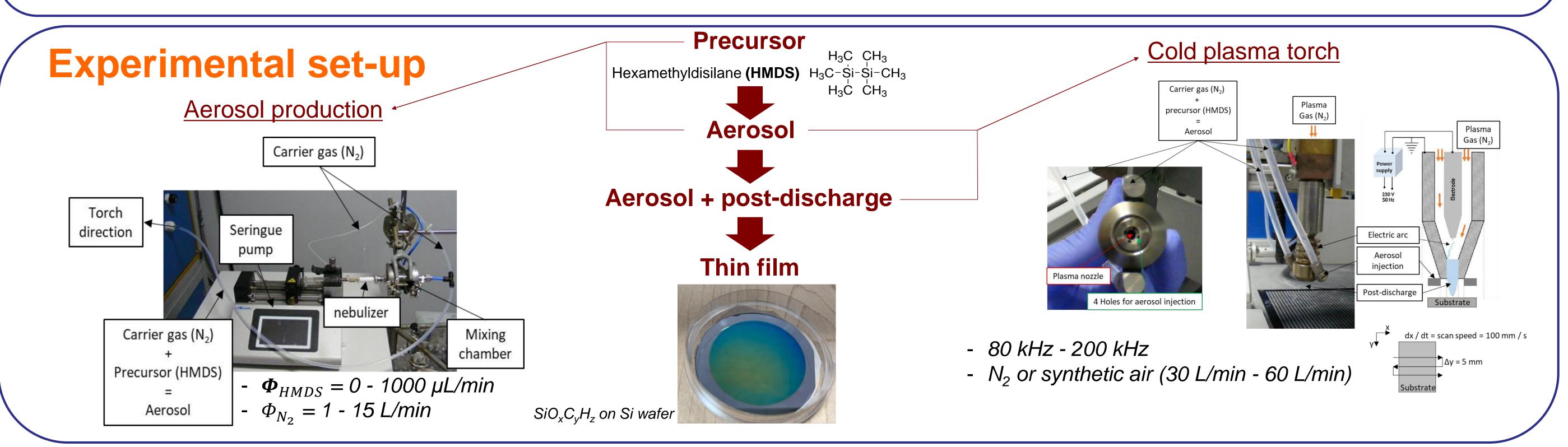
## Context

In this study, a non-thermal atmospheric pressure plasma torch from AcXys Plasma Technologies is coupled with an aerosol injection

This process offers an easy and robust solution to generate low temperature post-discharge in air or nitrogen

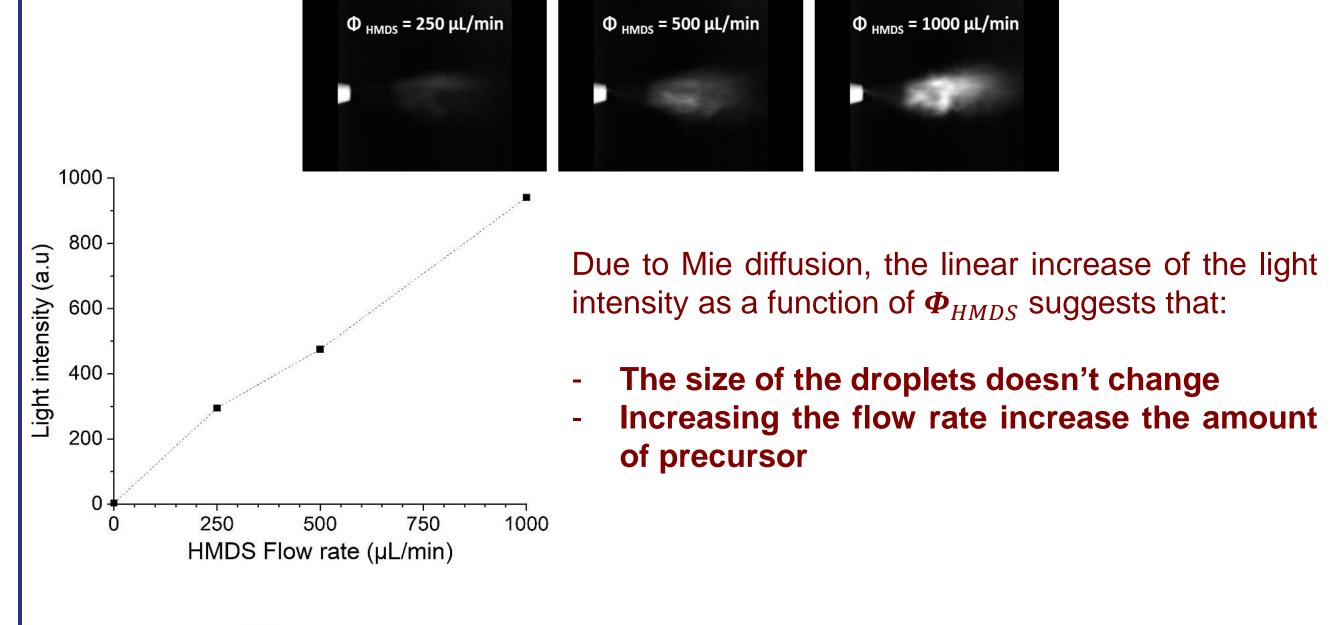
It is suitable for surface activation and for thin film deposition on flat or 3D complex substrates for in-line production

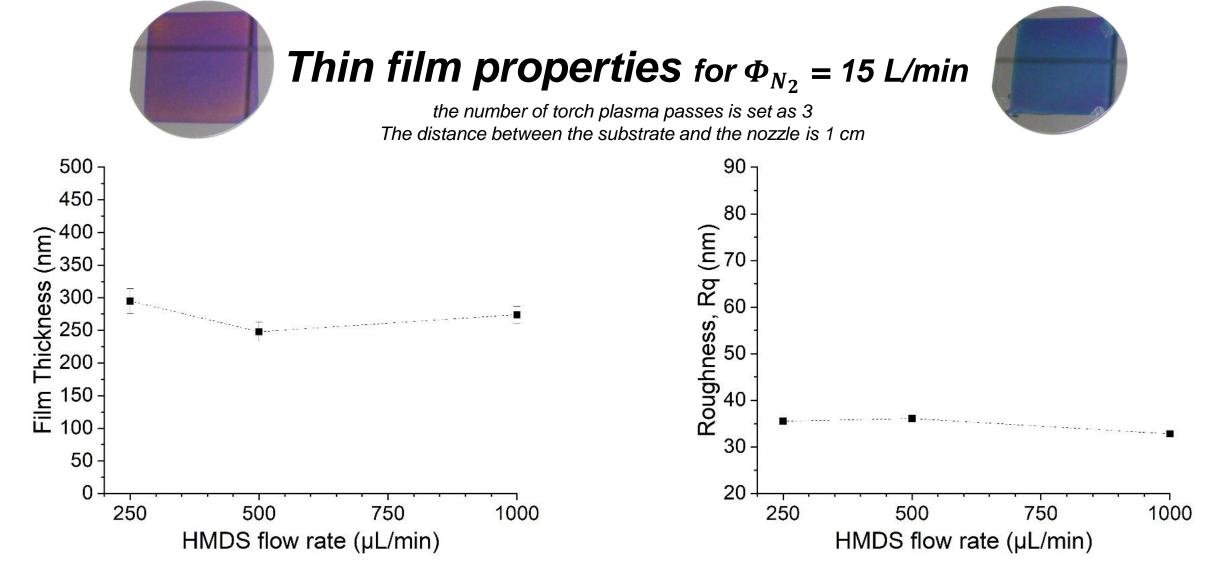
The influence of process parameters (carrier gas and precursor flow rate) on the thin film properties are investigated



## Influence of precursor flow rate (HMDS)

#### Photo of the aerosol at the nebulizer exit

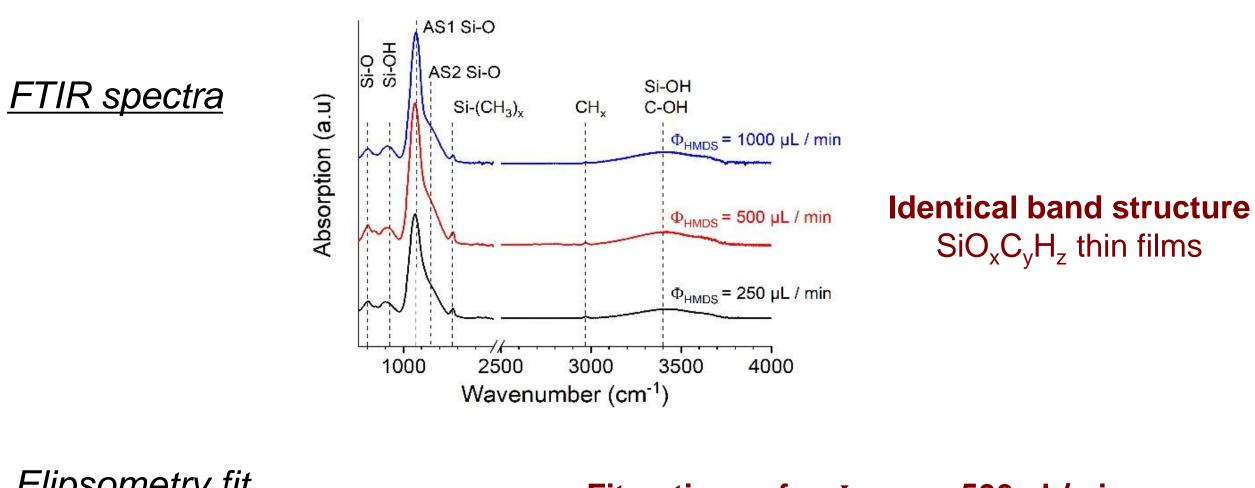




The thin film thickness and roughness are faintly affected by  $\Phi_{
m HMDS}$ 

#### **Hypothesis:**

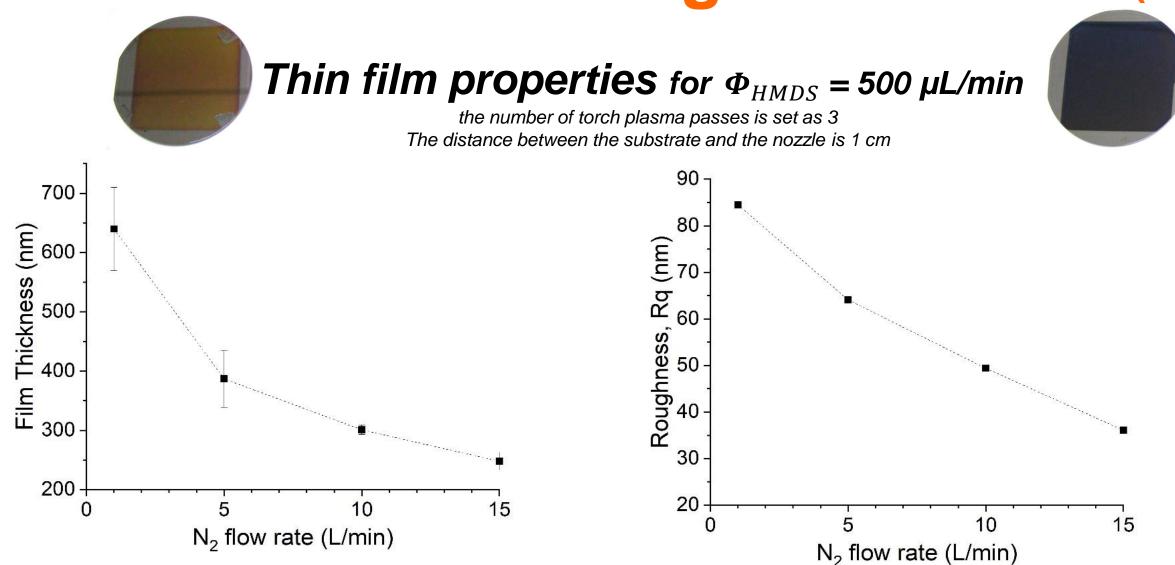
- Mass balance ↓ (reactivity or adhesive problems ?)
- Plasma/droplet interaction



Elipsometry fit with 2 phases (SiO<sub>2</sub> + void)

Fit optimum for  $\Phi_{HMDS}$  = 500 µL/min  $\rightarrow$  SiO<sub>2</sub>-like thin film

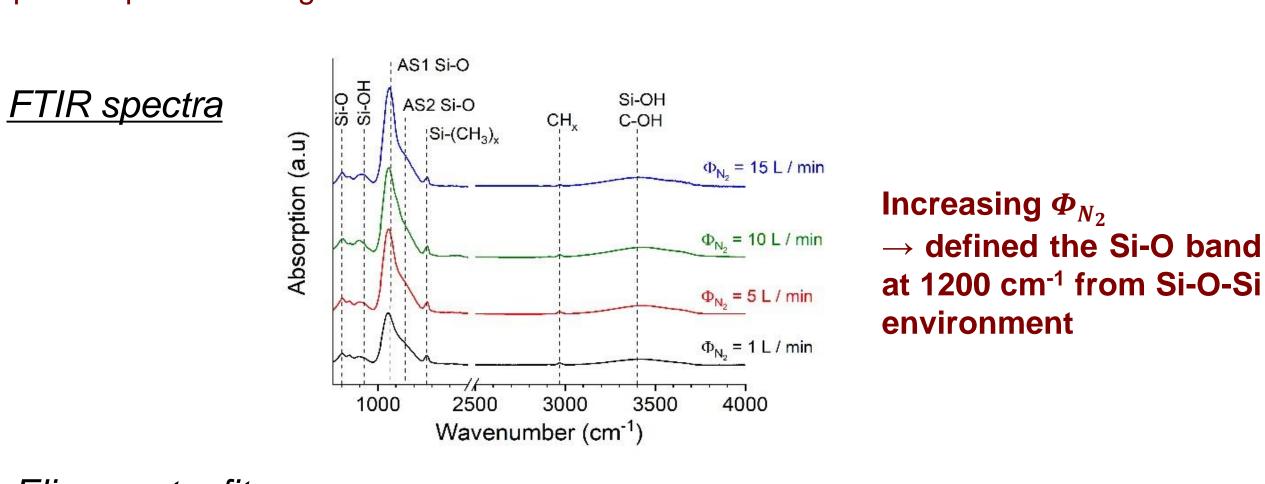
# Influence of carrier gas flow rate (N2)



The thin film thickness and roughness decrease with  $\Phi_{\mathrm{HMDS}}$ 

#### **Hypothesis:**

- Densification of the thin film
- Modification of the aerosol density and/or higher precursor dissociation at the center of the plasma post discharge



Elipsometry fit with 2 phases (SiO<sub>2</sub> + void)

Increasing  $\Phi_{N_2}$   $\rightarrow$  tend toward SiO<sub>2</sub>-like thin film

### Conclusion

- ► Elaboration of SiO<sub>x</sub>C<sub>y</sub>H<sub>z</sub> thin films from aerosol-assisted atmospheric pressure plasma
- ➤ **High deposition rate** (from ≈80 to 200 nm/passing at 100mm/s)
- > Increasing the precursor flow rate (HMDS):
  - Increase the amount of the droplets precursor but not their size
  - Faintly modified thin film properties
- $\triangleright$  Increasing the carrier gas flow rate (N<sub>2</sub>):
  - Densify the thin film (↓ thickness and ↓ roughness)
  - Modify the film chemistry (SiO<sub>x</sub>C<sub>y</sub>H<sub>z</sub> → SiO<sub>2</sub>-like)

This set-up open up news perspective for various precursors





